

GENERAL DESCRIPTION

Planar passivated high commutation triacs in a plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

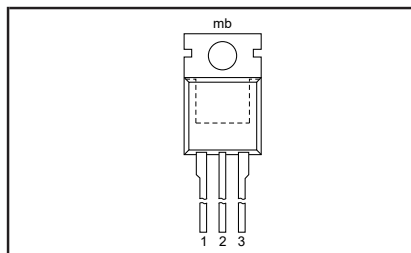
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{DRM}	BTA212- Repetitive peak off-state voltages	500B 500	600B 600	800B 800	V
$I_{T(RMS)}$	RMS on-state current	12	12	12	A
I_{TSM}	Non-repetitive peak on-state current	95	95	95	A

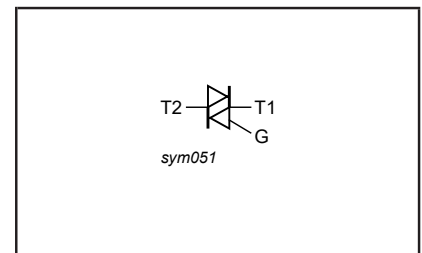
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500	-600	-800	
V_{DRM}	Repetitive peak off-state voltages		-	500 ¹	600 ¹	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 99\text{ }^\circ\text{C}$	-	12			A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25\text{ }^\circ\text{C}$ prior to surge	-	95			A
I^2t	I^2t for fusing	$t = 20\text{ ms}$	-	105			A
dI_T/dt	Repetitive rate of rise of on-state current after triggering	$t = 16.7\text{ ms}$	-	45			A ² s
		$t = 10\text{ ms}$	-	100			A/ μs
I_{GM}	Peak gate current	$I_{TM} = 20\text{ A}; I_G = 0.2\text{ A};$ $dI_G/dt = 0.2\text{ A}/\mu\text{s}$	-	2			A
V_{GM}	Peak gate voltage		-	5			V
P_{GM}	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
T_{stg}	Storage temperature		-40	150			$^\circ\text{C}$
T_j	Operating junction temperature		-	125			$^\circ\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	full cycle	-	-	1.5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	half cycle in free air	-	60	2.0	K/W

STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current ²	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$				
		T2+ G+	2	18	50	mA
		T2+ G-	2	21	50	mA
		T2- G-	2	34	50	mA
I_L	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$				
		T2+ G+	-	31	60	mA
		T2+ G-	-	34	90	mA
		T2- G-	-	30	60	mA
I_H	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	31	60	mA
V_T	On-state voltage	$I_T = 17\text{ A}$	-	1.3	1.6	V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	0.7	1.5	V
I_D	Off-state leakage current	$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ °C}$ $V_D = V_{DRM(max)}; T_j = 125\text{ °C}$	0.25	0.4	-	V
			-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ exponential waveform; gate open circuit	1000	4000	-	V/ μ s
dI_{com}/dt	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}; T_j = 125\text{ °C}; I_{T(RMS)} = 12\text{ A};$ without snubber; gate open circuit	-	24	-	A/ms
t_{gt}	Gate controlled turn-on time	$I_{TM} = 12\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A};$ $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μ s

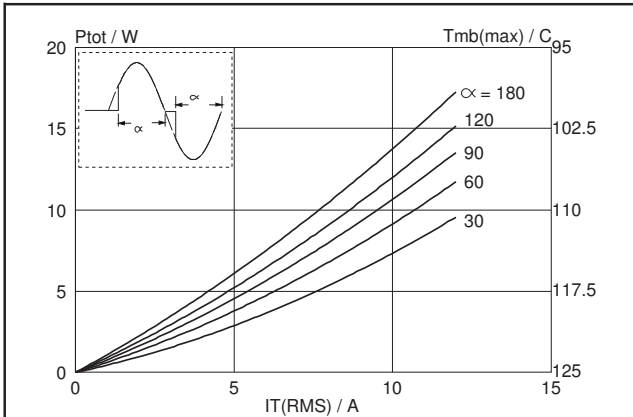


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

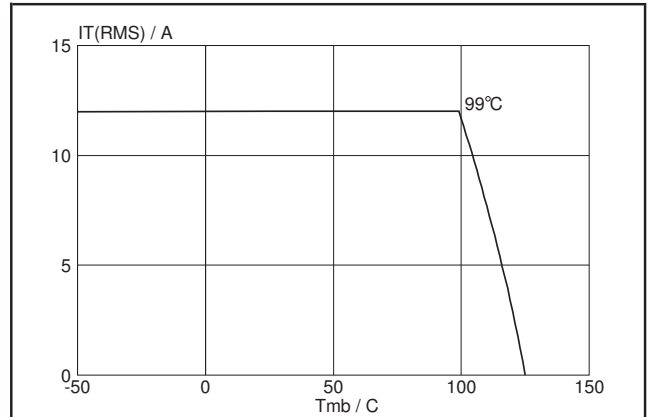


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

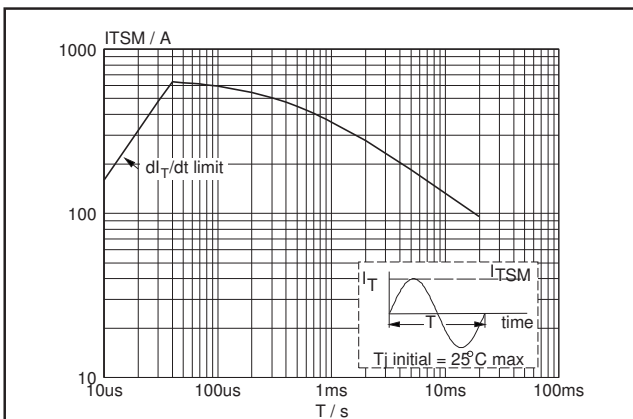


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 20$ ms.

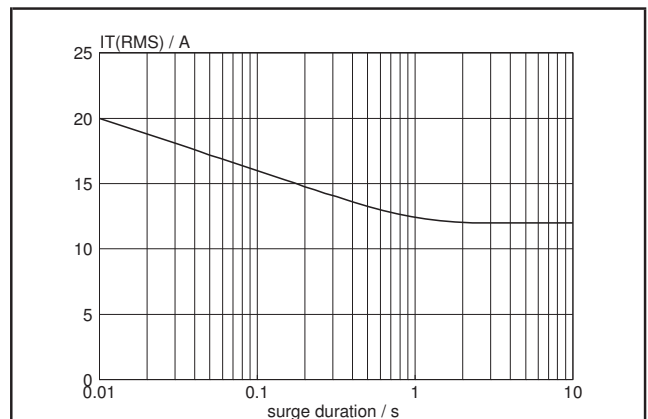


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50$ Hz; $T_{mb} \leq 99^\circ\text{C}$.

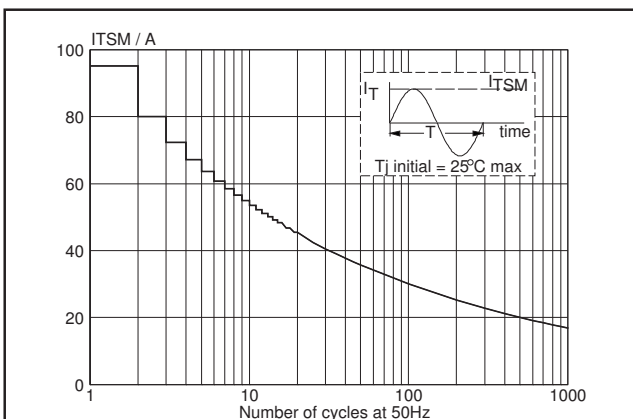


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50$ Hz.

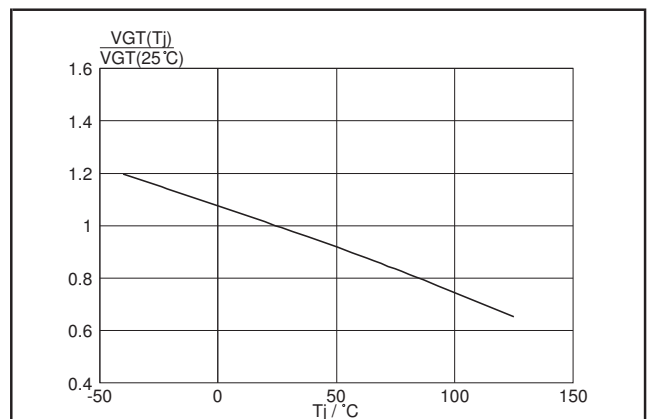
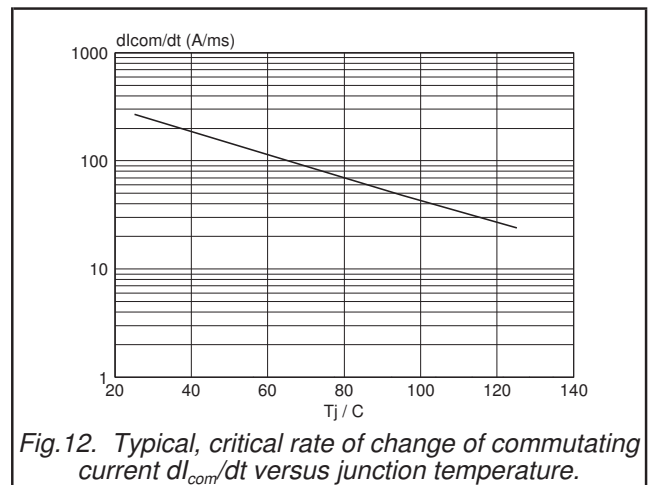
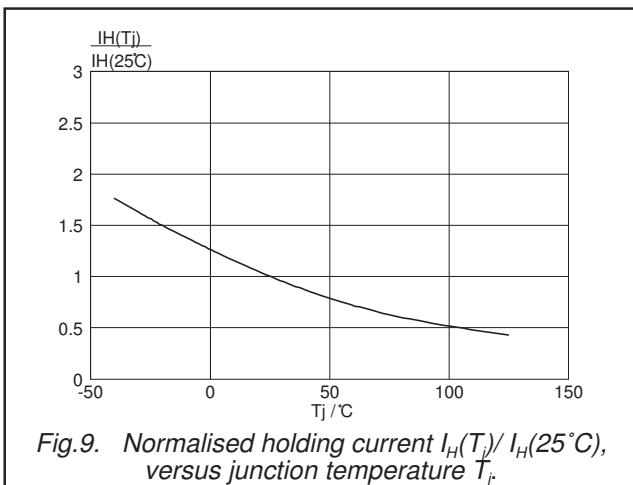
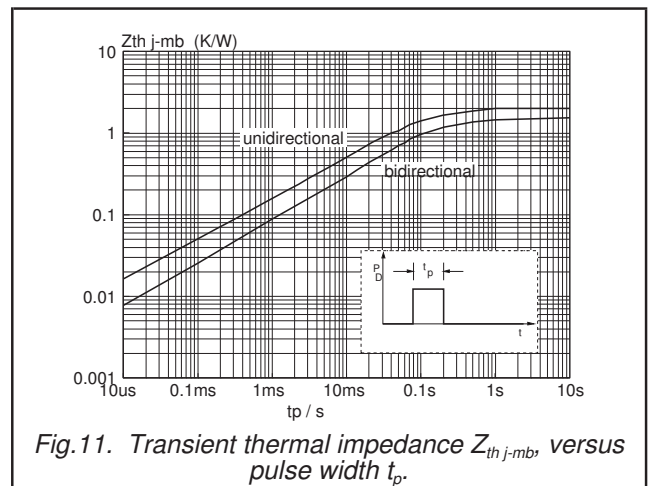
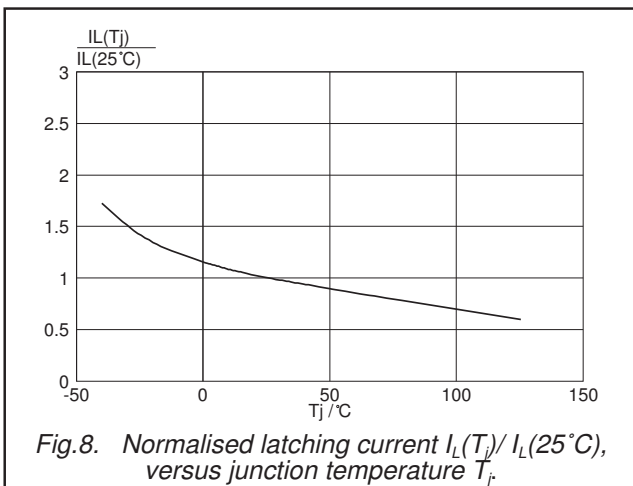
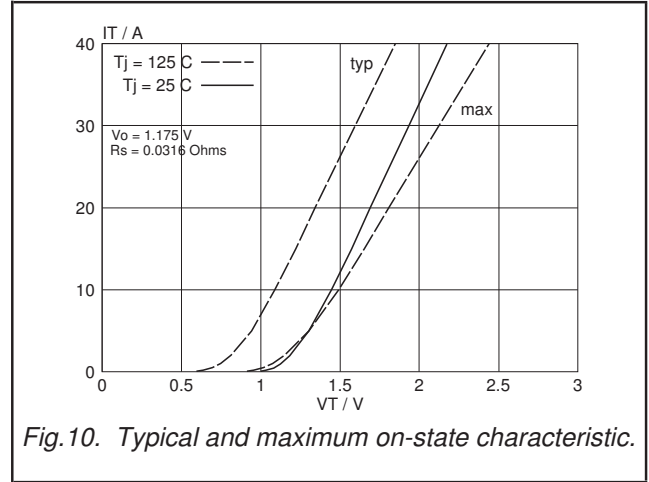
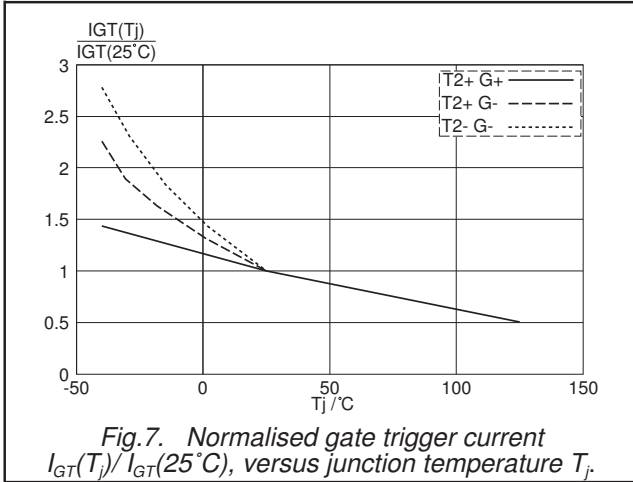


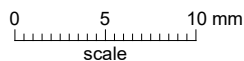
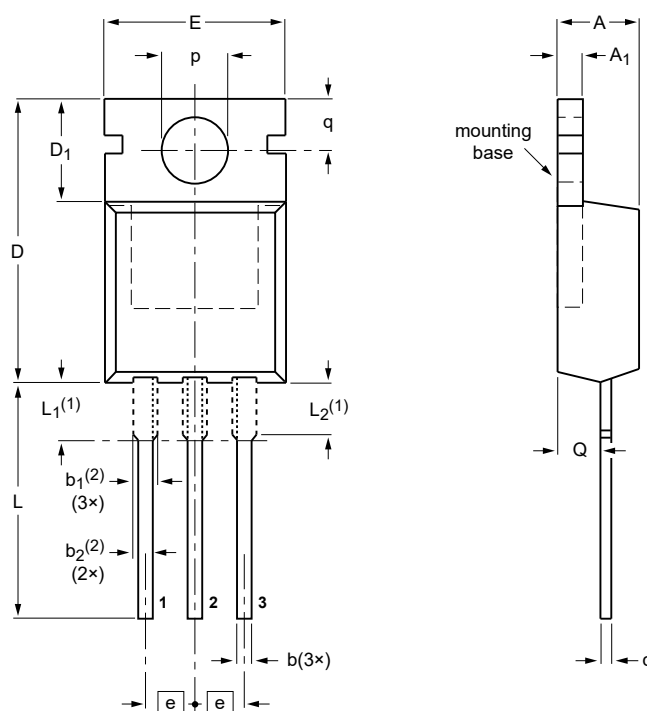
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j) / V_{GT}(25^\circ\text{C})$, versus junction temperature T_j .



MECHANICAL DATA

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13